REMARKS

Claims 1 and 14-17 have been amended, claims 19-52 have been canceled and new claims 53-62 have been added. Consideration of the application as amended is requested.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page(s) are captioned "**Version with markings to show changes made**."

The amendments to the specification and claims and new claims 53-62 are supported at least by text appearing at p. 4, line 14 through p. 13, line 11 of the application as originally filed. No new matter is added by the amendments to the specification or claims, or by new claims 53-62.

This application is believed to be in condition for allowance and action to that end is requested. The Examiner is requested to telephone the undersigned in the event that the next office action is one other than a Notice of Allowance. The undersigned is available during normal business hours (Pacific Time Zone).

Respectfully submitted,

Dated: Feb. 22, 2002 By: [signature]

Frederick M. Fliegel, Ph.D.
Reg. No. 36,138

Version with markings to show changes made.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 09/389,533
Priority Filing Date ....September 2, 1999
Inventor ....Alan R. Reinberg
Assignee.. Micron Technology, Inc.
Priority Group Art Unit 2823
Priority Examiner .... T. Pham
Attorney's Docket No. MI22-1952
Title: Methods of Forming Capacitors and Resultant Capacitor Structures

37 CFR §1.121(b)(1)(iii) AND 37 CFR §1.121(c)(1)(ii) FILING REQUIREMENTS TO ACCOMPANY PRELIMINARY AMENDMENT

Deletions are bracketed, additions are underlined.

In the Specification

At page 1, the following text has been inserted:

CROSS REFERENCE TO RELATED APPLICATION

This patent application is a Continuation Application of U.S. Patent Application Serial No. 09/389,533, filed September 2, 1999, entitled "Methods Of Forming Capacitors and Resultant Capacitor Structures", naming Alan R. Reinberg as inventor.

In the Claims

1. (Amended) A method of forming a capacitor comprising:

forming a capacitor storage node layer over a substrate, the capacitor storage node layer having an uppermost rim defining an opening into an interior volume; and

forming a cap by capping at least a portion of the rim within the interior volume by forming a material which is different from the capacitor storage node layer over the rim portion, said material as received at least over the rim portion not functioning primarily as a capacitor dielectric material for the capacitor [; and

after the capping of the rim, forming a capacitor dielectric region and a cell electrode layer over the capacitor storage node layer].

14. (Amended) A method of forming a capacitor comprising:

forming a capacitor storage node layer over a substrate, the capacitor storage node layer having an uppermost rim defining an opening into an interior volume; and

forming a layer of material over the uppermost rim within the interior volume [; and

anisotropically etching the layer of material].

15. (Amended) The method of claim 14, [wherein said etching comprises] <u>further comprising anisotropically</u> etching said layer sufficient to leave a portion of the material occluding the opening.

16. (Amended) The method of claim 14, [wherein said etching [comprises] <u>further comprising anisotropically</u> etching said layer sufficient to leave a portion of the material extending into the interior volume.

17. (Amended) The method of claim 14, [wherein said etching comprises] <u>further comprising anisotropically</u> etching said layer sufficient to leave a portion of the material extending into the interior volume and occluding the opening.

Claims 19-52 have been canceled and claims 53-62 have been added.

END OF DOCUMENT